

Masaaki A Tanaka

List of Publications by Year in descending order

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docs citations

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times ranked

3139
citing authors

#	ARTICLE	IF	CITATIONS
1	A spin metal-oxide-semiconductor field-effect transistor using half-metallic-ferromagnet contacts for the source and drain. Applied Physics Letters, 2004, 84, 2307-2309.	3.3	381
2	(GaMn)As: GaAs-based III-V diluted magnetic semiconductors grown by molecular beam epitaxy. Journal of Crystal Growth, 1997, 175-176, 1063-1068.	1.5	183
3	Electromotive force and huge magnetoresistance in magnetic tunnel junctions. Nature, 2009, 458, 489-492.	27.8	164
4	Nearly non-magnetic valence band of the ferromagnetic semiconductor GaMnAs. Nature Physics, 2011, 7, 342-347.	16.7	128
5	Ferromagnet (MnAs)/III-V semiconductor hybrid structures. Semiconductor Science and Technology, 2002, 17, 327-341.	2.0	127
6	Magnetic and transport properties of III-V based magnetic semiconductor (GaMn)As: Growth condition dependence. Applied Physics Letters, 1999, 74, 398-400.	3.3	116
7	Formation of planar superlattice states in new grid-inserted quantum well structures. Applied Physics Letters, 1989, 54, 1326-1328.	3.3	113
8	MOS-Based Spin Devices for Reconfigurable Logic. IEEE Transactions on Electron Devices, 2007, 54, 961-976.	3.0	98
9	Recent progress in III-V based ferromagnetic semiconductors: Band structure, Fermi level, and tunneling transport. Applied Physics Reviews, 2014, 1, 011102.	11.3	96
10	High-temperature ferromagnetism in heavily Fe-doped ferromagnetic semiconductor (Ga,Fe)Sb. Applied Physics Letters, 2016, 108, .	3.3	94
11	A Silicon-Based Approach to Oligoarenes by Iterative Cross-Coupling Reactions of Halogenated Organo[(2-hydroxymethyl)phenyl]dimethylsilanes. Journal of the American Chemical Society, 2007, 129, 11694-11695.	13.7	84
12	Growth and characterization of n-type electron-induced ferromagnetic semiconductor (In,Fe)As. Applied Physics Letters, 2012, 101, .	3.3	78
13	Unveiling the impurity band induced ferromagnetism in the magnetic semiconductor (Ga,Mn)As. Physical Review B, 2014, 89, .	3.2	76
14	Epitaxial growth and properties of III-V magnetic semiconductor (GaMn)As and its heterostructures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2267.	1.6	75
15	Quantum transport evidence of Weyl fermions in an epitaxial ferromagnetic oxide. Nature Communications, 2020, 11, 4969.	12.8	71
16	Tunneling magnetoresistance in fully epitaxial MnAs/AlAs/MnAs ferromagnetic tunnel junctions grown on vicinal GaAs(111)B substrates. Applied Physics Letters, 2002, 80, 1969-1971.	3.3	67
17	Magnetic properties and intrinsic ferromagnetism in $\text{Ga}_{1-x}\text{Mn}_x\text{As}$ semiconductors. Physical Review B, 2015, 92, .		
18	Quantum size effect and tunneling magnetoresistance in ferromagnetic-semiconductor quantum heterostructures. Physical Review B, 2007, 75, .	3.2	62

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19	Magneto-optical and magnetotransport properties of heavily Mn-doped GaMnAs. Applied Physics Letters, 2007, 90, 112503.	3.3	56
20	Photocyclization Reaction of Diarylethene~Perylenebisimide Dyads upon Irradiation with Visible (>500 nm) Light. Journal of Physical Chemistry C, 2009, 113, 11623-11627.	3.1	54
21	Novel Reconfigurable Logic Gates Using Spin Metal~Oxide~Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2004, 43, 6032-6037.	1.5	53
22	Epitaxial ferromagnetic thin films and superlattices of Mn-based metallic compounds on GaAs. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 31, 117-125.	3.5	52
23	Precipitation of Amorphous Ferromagnetic Semiconductor Phase in Epitaxially Grown Mn-Doped Ge Thin Films. Japanese Journal of Applied Physics, 2005, 44, L1426-L1429.	1.5	52
24	Electron effective mass in n-type electron-induced ferromagnetic semiconductor (In,Fe)As: Evidence of conduction band transport. Applied Physics Letters, 2012, 101, .	3.3	51
25	Efficient full spin~orbit torque switching in a single layer of a perpendicularly magnetized single-crystalline ferromagnet. Nature Communications, 2019, 10, 2590.	12.8	51
26	Long spin-relaxation time in a single metal nanoparticle. Nature Nanotechnology, 2010, 5, 593-596.	31.5	49
27	Spintronics: recent progress and tomorrow's challenges. Journal of Crystal Growth, 2005, 278, 25-37.	1.5	48
28	A spin metal-oxide-semiconductor field-effect transistor (spin MOSFET) with a ferromagnetic semiconductor for the channel. Journal of Applied Physics, 2005, 97, 10D503.	2.5	48
29	Fluorescence photoswitching of a diarylethene~perylenebisimide dyad based on intramolecular electron transfer. Photochemical and Photobiological Sciences, 2010, 9, 181.	2.9	47
30	Invisible photochromism of diarylethene derivatives. Chemical Communications, 2008, , 3924.	4.1	46
31	Synthesis of Biaryls and Oligoarenes Using Aryl[2-(hydroxymethyl)phenyl]dimethylsilanes. Bulletin of the Chemical Society of Japan, 2010, 83, 554-569.	3.2	45
32	Electrical and Optical Control of Ferromagnetism in III-V Semiconductor Heterostructures at High Temperature (~100 K). Japanese Journal of Applied Physics, 2004, 43, L233-L236.	1.5	44
33	(Ga,Fe)Sb: A p-type ferromagnetic semiconductor. Applied Physics Letters, 2014, 105, .	3.3	43
34	Magnetic properties of heavily Mn-doped quaternary alloy ferromagnetic semiconductor (InGaMn)As grown on InP. Applied Physics Letters, 2003, 83, 2175-2177.	3.3	42
35	Valence-Band Structure of the Ferromagnetic Semiconductor GaMnAs Studied by Spin-Dependent Resonant Tunneling Spectroscopy. Physical Review Letters, 2010, 104, 167204.	7.8	42
36	Crystalline anisotropic magnetoresistance with two-fold and eight-fold symmetry in (In,Fe)As ferromagnetic semiconductor. Applied Physics Letters, 2012, 100, .	3.3	42

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55	Digging up bulk band dispersion buried under a passivation layer. Applied Physics Letters, 2012, 101, .	3.3	26
56	Control of ferromagnetism by manipulating the carrier wavefunction in ferromagnetic semiconductor (In,Fe)As quantum wells. Applied Physics Letters, 2014, 104, 042404.	3.3	26
57	Improvement of saturation magnetization of Fe nanoparticles by post-annealing in a hydrogen gas atmosphere. Journal of Applied Physics, 2015, 117, .	2.5	26
58	Magnetic properties of MnAs nanoclusters embedded in a GaAs semiconductor matrix. Journal of Magnetism and Magnetic Materials, 2007, 310, 1932-1934.	2.3	25
59	Phase decomposition diagram of magnetic alloy semiconductor. Journal of Applied Physics, 2011, 109, 073919.	2.5	24
60	Spin injection into silicon in three-terminal vertical and four-terminal lateral devices with Fe/Mg/MgO/Si tunnel junctions having an ultrathin Mg insertion layer. Physical Review B, 2017, 96, .	3.2	24
61	Recent progress in ferromagnetic semiconductors and spintronics devices. Japanese Journal of Applied Physics, 2021, 60, 010101.	1.5	24
62	Growth and Properties of Quaternary Alloy Magnetic Semiconductor (InGaMn)As. Japanese Journal of Applied Physics, 2002, 41, L24-L27.	1.5	23
63	Waveguide-Based 1.5 μm Optical Isolator Based on Magneto-Optic Effect in Ferromagnetic MnAs. Japanese Journal of Applied Physics, 2007, 46, 205-210.	1.5	23
64	Suppression of the field-like torque for efficient magnetization switching in a spin-orbit ferromagnet. Nature Electronics, 2020, 3, 751-756.	26.0	23
65	Efficient spin-to-charge current conversion in an all-epitaxial single-crystal perovskite-oxide heterostructure of $\text{La}_{0.67}\text{Sr}_{0.33}\text{MnO}_3/\text{SrTiO}_3$.	3.6	23
66	Spin-dependent transport properties of a GaMnAs-based vertical spin metal-oxide-semiconductor field-effect transistor structure. Applied Physics Letters, 2015, 107, .	3.3	22
67	Tunneling magnetoresistance of MnAs thin film/GaAs/AlAs/GaAs:MnAs nanoclusters and its AlAs barrier thickness dependence. Applied Physics Letters, 2006, 89, 242106.	3.3	21
68	Magnetoresistance of a Spin Metal-Oxide Semiconductor Field-Effect Transistor with Ferromagnetic MnAs Source and Drain Contacts. Japanese Journal of Applied Physics, 2010, 49, 113001.	1.5	21
69	Atomic-scale surface morphology of epitaxial ferromagnetic MnAs thin films grown on vicinal GaAs(111)B substrates. Journal of Applied Physics, 2001, 89, 6677-6679.	2.5	20
70	Spin polarized tunneling in V -based heterostructures with a ferromagnetic MnAs thin film and GaAs:MnAs nanoclusters. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 416-418.	2.7	20
71	Schottky barrier height of ferromagnet/Si(001) junctions. Applied Physics Letters, 2006, 89, 072110.	3.3	20
72	Spin-dependent transport properties in GaMnAs-based spin hot-carrier transistors. Applied Physics Letters, 2007, 90, 162505.	3.3	20

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73	Valence-band structure of ferromagnetic semiconductor (In,Ga,Mn)As. Physical Review B, 2012, 86, .	3.2	20
74	Room-temperature local ferromagnetism and its nanoscale expansion in the ferromagnetic semiconductor Ge _{1-x} Fe _x . Scientific Reports, 2016, 6, 23295.	3.3	20
75	High-mobility 2D Hole Gas at a SrTiO ₃ Interface. Advanced Materials, 2020, 32, e1906003.	21.0	20
76	Magneto-optical and magnetotransport properties of amorphous ferromagnetic semiconductor Ge _{1-x} Mn _x thin films. Applied Physics Letters, 2008, 93, .	3.3	19
77	Heavily Fe-doped ferromagnetic semiconductor (In,Fe)Sb with high Curie temperature and large magnetic anisotropy. Applied Physics Express, 2019, 12, 103004.	2.4	19
78	Electron spin and momentum lifetimes in two-dimensional Si accumulation channels: Demonstration of Schottky-barrier spin metal-oxide-semiconductor field-effect transistors at room temperature. Physical Review B, 2019, 99, .	3.2	19
79	Thickness-dependent quantum transport of Weyl fermions in ultra-high-quality SrRuO ₃ films. Applied Physics Letters, 2021, 118, 092408.	3.3	19
80	Spin-valve effect by ballistic transport in ferromagnetic metal (MnAs)/semiconductor (GaAs) hybrid heterostructures. Physical Review B, 2008, 77, .	3.2	18
81	Studies on spintronics-related thin films using synchrotron-radiation-based Mössbauer spectroscopy. Hyperfine Interactions, 2013, 217, 127-135.	0.5	18
82	Magnetic anisotropy control by applying an electric field to the side surface of ferromagnetic films. Scientific Reports, 2017, 7, 5618.	3.3	18
83	Structural and transport properties of highly Ru-deficient SrRu _{0.7} O ₃ thin films prepared by molecular beam epitaxy: Comparison with stoichiometric SrRuO ₃ . AIP Advances, 2021, 11, .	1.3	18
84	Annealing-induced enhancement of ferromagnetism and nanoparticle formation in the ferromagnetic semiconductor GeFe . Physical Review B, 2014, 90, .	3.2	17
85	Anomalous Fermi level behavior in GaMnAs at the onset of ferromagnetism. Applied Physics Letters, 2013, 103, 032411.	3.3	16
86	Electronic structure of the high- T_C ferromagnetic semiconductor (Ga,Fe)Sb: X-ray magnetic circular dichroism and resonance photoemission spectroscopy studies. Physical Review B, 2019, 100, .	3.2	16
87	Hybridization between the ligand p band and d orbitals in the p -type ferromagnetic semiconductor (Ga,Fe)Sb. Physical Review B, 2020, 101, .	3.2	16
88	Quantum-level control in a III-V-based ferromagnetic-semiconductor heterostructure with a GaMnAs quantum well and double barriers. Applied Physics Letters, 2010, 96, 052505.	3.3	15
89	Sudden restoration of the band ordering associated with the ferromagnetic phase transition in a semiconductor. Nature Communications, 2016, 7, 12013.	12.8	15
90	In-plane to perpendicular magnetic anisotropy switching in heavily-Fe-doped ferromagnetic semiconductor (Ga,Fe)Sb with high Curie temperature. Physical Review Materials, 2019, 3, .	2.4	15

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91	Epitaxial Growth and Magnetic Properties of Ferromagnetic Semiconductor Ge _{1-x} Fe _x Thin Films Epitaxially Grown on Si(001) Substrates. Japanese Journal of Applied Physics, 2008, 47, 7108.	1.5	14
92	Interplay between strain, quantum confinement, and ferromagnetism in strained ferromagnetic semiconductor (In,Fe)As thin films. Applied Physics Letters, 2014, 104, .	3.3	14
93	Spin transport in Si-based spin metal-oxide-semiconductor field-effect transistors: Spin drift effect in the inversion channel and spin relaxation in the $\frac{3.2}{4} \times \frac{14}{7}$ source/drain regions. Physical Review B, 2020, 102, .	3.2	14
94	Reconfigurable Logic Gates Using Single-Electron Spin Transistors. Japanese Journal of Applied Physics, 2007, 46, 6579-6585.	1.5	13
95	Properties of Heavily Mn-doped GaMnAs with Curie Temperature of 172.5 K. Journal of Superconductivity and Novel Magnetism, 2007, 20, 417-420.	1.8	13
96	Current-induced dynamics of bubble domains in perpendicularly magnetized TbFeCo wires. Applied Physics Express, 2015, 8, 073002.	2.4	13
97	Origin of the broad three-terminal Hanle signals in Fe/SiO ₂ /Si tunnel junctions. Applied Physics Letters, 2015, 107, 032407.	3.3	12
98	Artificial control of the bias-voltage dependence of tunnelling-anisotropic magnetoresistance using quantization in a single-crystal ferromagnet. Nature Communications, 2017, 8, 15387.	12.8	12
99	Reduction of the magnetic dead layer and observation of tunneling magnetoresistance in La _{0.67} Sr _{0.33} MnO ₃ -based heterostructures with a LaMnO ₃ layer. Applied Physics Letters, 2017, 110, .	3.3	12
100	Magneto-optical spectra and the presence of an impurity band in <i>p</i> -type ferromagnetic semiconductor (Ga,Fe)Sb with high Curie temperature. APL Materials, 2019, 7, .	5.1	12
101	Elemental Topological Dirac Semimetal In_2Te_3 with High Quantum Mobility. Advanced Materials, 2021, 33, e2104645.	21.0	12
102	Structural and magnetic properties of Ge _{1-x} Mn _x thin films grown on Ge (001) substrates. Journal of Applied Physics, 2011, 110, 073903.	2.5	11
103	Origin of the large positive magnetoresistance of G_{e}^{Mn} thin films. Applied Physics Letters, 2011, 99, 072101.	3.2	11
104	Evidence for Spin-Triplet Electron Pairing in the Proximity-Induced Superconducting State of an Fe-Doped InAs Semiconductor. Physical Review Letters, 2019, 122, 107001.	7.8	11
105	Real time observation of reconstruction transitions on GaAs (111)B surface by scanning electron microscopy. Applied Physics Letters, 1996, 69, 565-567.	3.3	10
106	A novel spin transistor based on spin-filtering in ferromagnetic barriers: a spin-filter transistor. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 996-1001.	2.7	10
107	Three-dimensional nanostructuring in YIG ferrite with femtosecond laser. Optics Letters, 2014, 39, 212.	3.3	10
108	Carrier transport properties of the Group-IV ferromagnetic semiconductor Ge _{1-x} Fe _x with and without boron doping. AIP Advances, 2014, 4, .	1.3	10

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109	Electronic structure near the Fermi level in the ferromagnetic semiconductor GaMnAs studied by ultrafast time-resolved light-induced reflectivity measurements. <i>Physical Review B</i> , 2016, 93, .	3.2	10
110	Electric-current-induced dynamics of bubble domains in a ferrimagnetic Tb/Co multilayer wire below and above the magnetic compensation point. <i>AIP Advances</i> , 2017, 7, .	1.3	10
111	Observation of the inverse spin Hall effect in the topological crystalline insulator SnTe using spin pumping. <i>Physical Review B</i> , 2017, 96, .	3.2	10
112	MBE growth process of ferromagnetic MnAs on Si(111) substrates. <i>Journal of Crystal Growth</i> , 2001, 227-228, 874-881.	1.5	9
113	Important role of the non-uniform Fe distribution for the ferromagnetism in group-IV-based ferromagnetic semiconductor GeFe. <i>Journal of Applied Physics</i> , 2014, 116, 173906.	2.5	9
114	Spin transport in nanoscale Si-based spin-valve devices. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	9
115	Ultrafast magnetization modulation induced by the electric field component of a terahertz pulse in a ferromagnetic-semiconductor thin film. <i>Scientific Reports</i> , 2018, 8, 6901.	3.3	9
116	Minority-spin impurity band in n -type (In,Fe)As: A materials perspective for ferromagnetic semiconductors. <i>Physical Review B</i> , 2021, 103, .	3.2	9
117	Cation distribution and magnetic properties in ultrathin $(\text{Ni}_{1-x}\text{Co}_x)\text{Fe}_2\text{O}_4$ ($x=0\text{--}1$) layers on Si(111) studied by soft x-ray magnetic circular dichroism. <i>Physical Review Materials</i> , 2018, 2, .	2.4	9
118	Simulation analysis of triboplasma generation using the particle-in-cell/Monte Carlo collision (PIC/MCC) method. <i>Journal Physics D: Applied Physics</i> , 2012, 45, 495203.	2.8	8
119	Spin-dependent tunneling transport in a ferromagnetic GaMnAs and un-doped GaAs double-quantum-well heterostructure. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	8
120	Thickness dependence of Morin transition temperature in iridium-doped hematite layers studied through nuclear resonant scattering. <i>Hyperfine Interactions</i> , 2017, 238, 1.	0.5	8
121	Large current modulation and tunneling magnetoresistance change by a side-gate electric field in a GaMnAs-based vertical spin metal-oxide-semiconductor field-effect transistor. <i>Scientific Reports</i> , 2018, 8, 7195.	3.3	8
122	Fe delta-doped (In,Fe)Sb ferromagnetic semiconductor thin films for magnetic-field sensors with ultrahigh Hall sensitivity. <i>Journal of Crystal Growth</i> , 2019, 511, 127-131.	1.5	8
123	Large terahertz magnetization response in ferromagnetic nanoparticles. <i>Applied Physics Letters</i> , 2019, 114, .	3.3	8
124	Direct observation of the magnetic ordering process in the ferromagnetic semiconductor $\text{Ga}_{1-x}\text{Mn}_x\text{As}$ via soft x-ray magnetic circular dichroism. <i>Journal of Applied Physics</i> , 2020, 128, .	2.5	8
125	Evolution of Fe impurity band state as the origin of high Curie temperature in the ferromagnetic semiconductor $(\text{Ga,Fe})\text{Sb}$. <i>Physical Review B</i> , 2020, 102, .	3.2	8
126	Epitaxial growth and magnetic properties of a new group-IV ferromagnetic semiconductor: $\text{Ge}_{1-x}\text{Fex}$. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 4110-4114.	0.8	7

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127	Single-Crystalline Ferromagnetic Alloy Semiconductor Ge _{1-x} Mn _x Grown on Ge(111). Applied Physics Express, 2010, 3, 123002.	2.4	7
128	Intrinsic magneto-optical spectra of GaMnAs. Applied Physics Letters, 2015, 106, .	3.3	7
129	Perpendicular magnetic anisotropy and tunneling conductivity of epitaxial cobalt-ferrite (0 0 1) films grown on nonmagnetic metal films. Journal of Magnetism and Magnetic Materials, 2019, 475, 721-726.	2.3	7
130	Room-temperature side-gate-induced current modulation in a magnetic tunnel junction with an oxide-semiconductor barrier for vertical spin MOSFET operation. Applied Physics Express, 2019, 12, 023009.	2.4	7
131	Epitaxial growth and properties of MnAs/GaAs/MnAs trilayer heterostructures. Journal of Magnetism and Magnetic Materials, 1999, 198-199, 719-721.	2.3	6
132	Large tunneling magnetoresistance (>70%) in GaMnAs/AlAs/GaMnAs single-barrier ferromagnetic semiconductor tunnel junctions. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 292-294.	2.7	6
133	Epitaxial growth and magnetic properties of single-crystal MnAs/AlAs/MnAs magnetic tunnel junctions on exact (111)B GaAs substrates: the effect of ultrathin GaAs buffer layers. Journal of Crystal Growth, 2003, 251, 317-322.	1.5	6
134	Hidden peculiar magnetic anisotropy at the interface in a ferromagnetic perovskite-oxide heterostructure. Scientific Reports, 2017, 7, 8715.	3.3	6
135	Electrical tuning of the band alignment and magnetoconductance in an n-type ferromagnetic semiconductor (In,Fe)As-based spin-Esaki diode. Applied Physics Letters, 2018, 112, .	3.3	6
136	Current-induced motion of bubble domains stabilised in nanowires with edge defects. Journal Physics D: Applied Physics, 2019, 52, 025001.	2.8	6
137	Inhomogeneity-induced high temperature ferromagnetism in n-type ferromagnetic semiconductor (In,Fe)As grown on vicinal GaAs substrates. Japanese Journal of Applied Physics, 2020, 59, 063002.	1.5	6
138	Temperature dependence of magnetic anisotropy in heavily Fe-doped ferromagnetic semiconductor (Ga,Fe)Sb. Journal of Applied Physics, 2020, 127, 023904.	2.5	6
139	Nearly ideal spin tunneling efficiency in $\text{Fe}/\text{MgO}/\text{Fe}/\text{Si}(001)$ junctions. Physical Review Materials, 2019, 3, .	2.4	6
140	Investigation of InAlAs Oxide/InP Metal-Oxide-Semiconductor Structures Formed by Wet Thermal Oxidation. Japanese Journal of Applied Physics, 2009, 48, 04C093.	1.5	5
141	Micromagnetic investigations of Néel- and Bloch-type skyrmion dynamics induced by spin Hall effect of cap layers. Japanese Journal of Applied Physics, 2017, 56, 098001.	1.5	5
142	Inverse spin-valve effect in nanoscale Si-based spin-valve devices. Journal of Applied Physics, 2017, 122, .	2.5	5
143	Large spin-valve effect in a lateral spin-valve device based on ferromagnetic semiconductor GaMnAs. Applied Physics Express, 2018, 11, 033003.	2.4	5
144	Large tunnel magnetoresistance in a fully epitaxial double-barrier magnetic tunnel junction of Fe/MgO/Fe β -Al ₂ O ₃ /Nb-doped SrTiO ₃ . AIP Advances, 2020, 10, 085115.	1.3	5

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145	Magnetization process of the insulating ferromagnetic semiconductor (Al,Fe)Sb. Physical Review B, 2020, 101, .	3.2	5
146	Ferromagnetism and giant magnetoresistance in zinc-blende FeAs monolayers embedded in semiconductor structures. Nature Communications, 2021, 12, 4201.	12.8	5
147	Photoelectron Spectroscopy and Magnetic Properties of Manganese Pnictides Nanocrystals Formed on Passivated GaAs Substrates. Japanese Journal of Applied Physics, 1999, 38, 373.	1.5	5
148	Simultaneous Measurement of γ -ray and Conversion Electron Mössbauer Spectra of Fe Films under Total Reflection Conditions Using Synchrotron Mössbauer Source. Journal of the Physical Society of Japan, 2020, 89, 054707.	1.6	5
149	Origin of perpendicular magnetic anisotropy in Co_xO thin films studied by x-ray magnetic circular and linear dichrois. Physical Review B. 2022, 105, .	3.2	5
150	Magneto-optical Kerr Effect of Semiconductor-Based Multilayer Structures Containing a GaAs:MnAs Granular Thin Film. Japanese Journal of Applied Physics, 2003, 42, L914-L917.	1.5	4
151	DLC coating on a micro-trench by bipolar PBI&D and analysis of plasma behaviour. Journal Physics D: Applied Physics, 2014, 47, 335306.	2.8	4
152	Visible-light electroluminescence in Mn-doped GaAs light-emitting diodes. Applied Physics Letters, 2014, 104, .	3.3	4
153	Quantum size effect in an Fe quantum well detected by resonant tunneling carriers injected from a p -type Ge semiconductor electrode. Applied Physics Letters, 2018, 112, .	3.3	4
154	Spin transport and spin accumulation signals in Si studied in tunnel junctions with a Fe/Mg ferromagnetic multilayer and an amorphous SiO_xN_y tunnel barrier. Applied Physics Letters, 2018, 112, .	3.3	4
155	Proximity-Induced Superconductivity in a Ferromagnetic Semiconductor (In,Fe)As. Journal of Physics: Conference Series, 2018, 969, 012036.	0.4	4
156	Alternation of Magnetic Anisotropy Accompanied by Metal-Insulator Transition in Strained Ultrathin Manganite Heterostructures. Physical Review Applied, 2021, 15, .	3.8	4
157	Molecular beam epitaxy growth, magnetic and structural properties of MnAs thin films grown on InP(001) and InGaAsP. Journal of Crystal Growth, 2007, 301-302, 615-618.	1.5	3
158	Fabrication, structural and magnetic properties of InAlMnAs and InAlAs:MnAs granular thin films. Journal of Crystal Growth, 2007, 301-302, 627-630.	1.5	3
159	Effects of laser irradiation on the self-assembly of MnAs nanoparticles in a GaAs matrix. Applied Physics Letters, 2012, 101, .	3.3	3
160	Epitaxial growth and characterization of n-type magnetic semiconductor (In,Co)As. Japanese Journal of Applied Physics, 2014, 53, 04EM05.	1.5	3
161	Tunneling magnetoresistance in trilayer structures composed of group-IV-based ferromagnetic semiconductor $\text{Ge}_{1-x}\text{Fe}_x$, MgO , and Fe. Applied Physics Express, 2016, 9, 123001.	2.4	3
162	Impurity band conduction in group-IV ferromagnetic semiconductor $\text{Ge}_{1-x}\text{Fe}_x$ with nanoscale fluctuations in Fe concentration. Journal of Applied Physics, 2018, 124, 113902.	2.5	3

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163	Improved performance of a GaMnAs-based vertical spin electric double-layer transistor. Japanese Journal of Applied Physics, 2018, 57, 090301.	1.5	3
164	Planar Nernst effect and Mott relation in (In,Fe)Sb ferromagnetic semiconductor. Journal of Applied Physics, 2018, 123, 175102.	2.5	3
165	Ultralow-Power Orbital-Controlled Magnetization Switching Using a Ferromagnetic Oxide Interface. Physical Review Applied, 2019, 12, .	3.8	3
166	Observation of quantum size effect at the conduction band bottom of n-type ferromagnetic semiconductor (In,Fe)As thin films. Applied Physics Express, 2019, 12, 073001.	2.4	3
167	Stabilization of Néel-type domain walls in multilayered magnetic wires using antiferromagnetic interlayer exchange coupling. Journal of Applied Physics, 2020, 128, 063902.	2.5	3
168	Spin transport in fully ferromagnetic p-n junctions. Journal of Applied Physics, 2022, 131, 013902.	2.5	3
169	Theoretical analysis of the inverse Edelstein effect at the LaAlO ₃ /SrTiO ₃ interface with an effective tight-binding model: important role of the second d _{xy} subband. Applied Physics Express, 2022, 15, 013005.	2.4	3
170	Growth and magnetic properties of epitaxial MnAs/NiAs/MnAs heterostructures grown on exact GaAs(111)B substrates. Journal of Crystal Growth, 2005, 278, 649-654.	1.5	2
171	Schottky barrier MOSFETs with epitaxial ferromagnetic MnAs/Si(001) source and drain: Post-growth annealing and transport characteristics. Journal of Crystal Growth, 2007, 301-302, 611-614.	1.5	2
172	Magnetoresistance enhanced by inelastic cotunneling in a ferromagnetic MnAs nanoparticle sandwiched by nonmagnetic electrodes. Journal of Applied Physics, 2012, 111, 063716.	2.5	2
173	High-field electroluminescence in semiconductor tunnel junctions with a Mn-doped GaAs layer. Journal of Applied Physics, 2014, 116, 113905.	2.5	2
174	Memristive magnetic tunnel junctions with MnAs nanoparticles. Applied Physics Letters, 2015, 107, 122404.	3.3	2
175	Spin-dependent transport and current modulation in a current-in-plane spin-valve field-effect transistor. Applied Physics Letters, 2016, 109, 152403.	3.3	2
176	Visible-light emission at room temperature in Mn-doped Si light-emitting diodes. Physical Review B, 2016, 93, .	3.2	2
177	Intrinsic transmission magnetic circular dichroism spectra of GaMnAs. AIP Advances, 2018, 8, 035009.	1.3	2
178	Growth and characterization of ferromagnetic Fe-doped GaSb quantum dots with high Curie temperature. APL Materials, 2020, 8, 091107.	5.1	2
179	Current-in-plane spin-valve magnetoresistance in ferromagnetic semiconductor (Ga,Fe)Sb heterostructures with high Curie temperature. Applied Physics Letters, 2020, 117, .	3.3	2
180	Enhancement of Room-Temperature Effective Spin Diffusion Length in a Si-Based Spin MOSFET With an Inversion Channel. IEEE Journal of the Electron Devices Society, 2020, 8, 807-812.	2.1	2

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181	Large magnetoresistance and spin-dependent output voltage in a lateral MnGa/CaAs/MnGa spin-valve device. Japanese Journal of Applied Physics, 2020, 59, SGGI08.	1.5	2
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